



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

11 A

Features

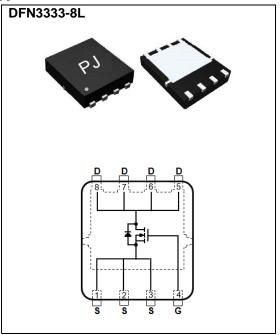
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@6A<72m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@3A<88m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	l _D	11	А	
	T _C =100°C		7		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	44		
Power Dissipation	T _C =25°C	Po	23.8	W	
	T _C =100°C		11.9		
Continuous Drain Current (Note 4)	T _A =25°C	I _D	3.7		
	T _A =70°C		2.9	Α	
Power Dissipation	T _A =25°C	Po	2.4	W	
	T _A =70°C		1.6		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	25	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	6.3	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA V _{DS} =V _{GS} , I _D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$		1	1.8	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =6A	-	53	72	mΩ
		V_{GS} =4.5V, I_{D} =3A	-	61	88	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V _{DS} =48V, I _D =6A, V _{GS} =10V ^(Note 1,2)	-	9.3	-	nC
Gate-Source Charge	Q_gs		-	2.2	-	
Gate-Drain Charge	Q_{gd}		-	1.9	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	509	-	pF
Output Capacitance	Coss		-	47	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	23	-	
Turn-On Delay Time	td _(on)	V_{DD} =30V, I_{D} =1A, V_{GS} =10V, R_{G} =3.3 Ω (Note 1,2)	-	3.2	-	ns
Turn-On Rise Time	t _r		-	9.7	-	
Turn-Off Delay Time	td _(off)		-	18.5	-	
Turn-Off Fall Time	t _f	$R_{G}=3.3\Omega$	-	6.4	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	11	А
Diode Forward Current	I _S		-			
Reverse Recovery Time	V_{SD}	I _S =1A, V _{GS} =0V	-	0.75	1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=1mH, I_{AS}=7A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

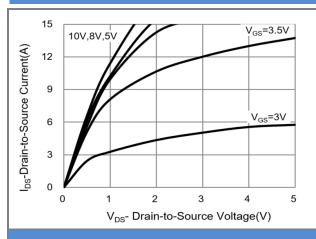


Fig.1 On-Region Characteristics

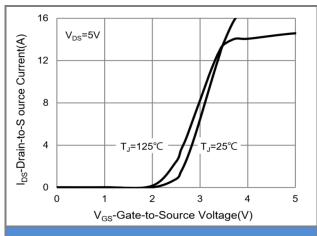


Fig.2 Transfer Characteristics

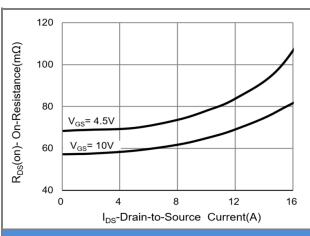


Fig.3 On-Resistance vs. Drain Current

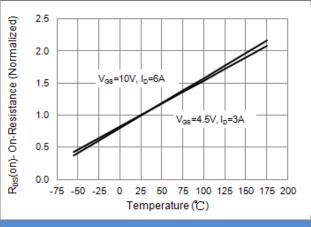


Fig.4 On-Resistance vs. Junction temperature

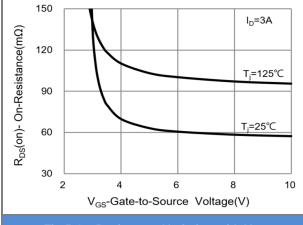


Fig.5 On-Resistance Variation with V_{GS}

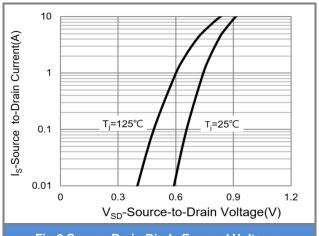


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

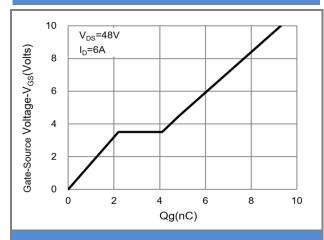


Fig.7 Gate-Charge Characteristics

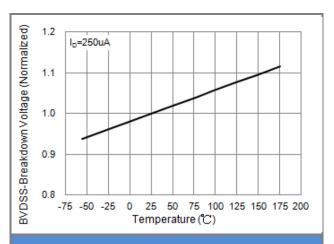


Fig.8 Breakdown Voltage Variation vs. Temperature

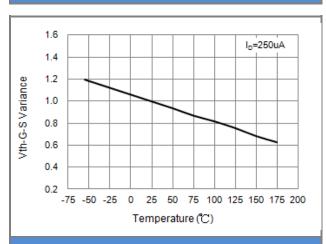


Fig.9 Threshold Voltage Variation with Temperature

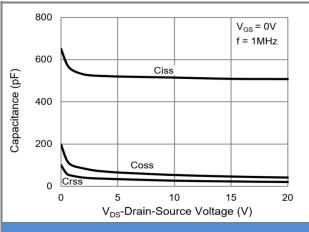
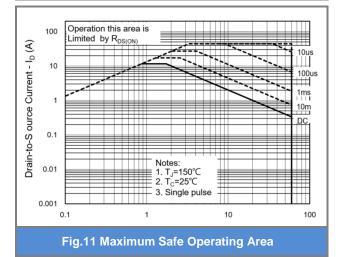


Fig.10 Capacitance vs. Drain-Source Voltage



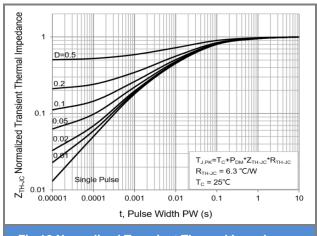


Fig.12 Normalized Transient Thermal Impedance

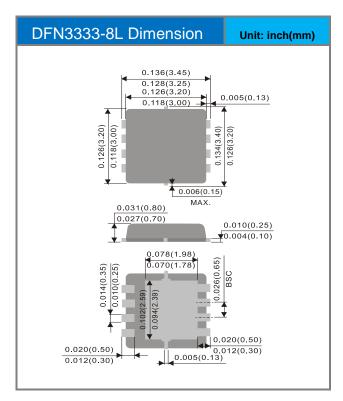


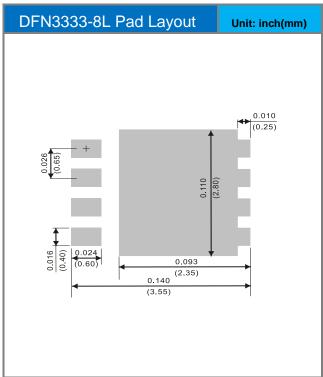


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ4460AP-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4460	Halogen free	

Packaging Information & Mounting Pad Layout









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